

General Description

The CD4053 is a triple single-pole double-throw (SPDT) analog switch, suitable for use as an analog or digital multiplexer/demultiplexer. Each switch has a digital select input (S_n), two independent inputs/ outputs (nY_0 and nY_1) and a common input/ output (nZ). All three switches share an enable input (\bar{E}). A HIGH on \bar{E} causes all switches into the high-impedance OFF-state, independent of S_n .

V_{DD} and V_{SS} are the supply voltage connections for the digital control inputs (S_n and \bar{E}). The V_{DD} to V_{SS} range is 3 V to 9 V. The analog inputs/ outputs (nY_0 , nY_1 , and nZ) can swing between V_{DD} as a positive limit and V_{EE} as a negative limit. $V_{DD} - V_{EE}$ may not exceed 9 V. Unused inputs must be connected to V_{DD} , V_{SS} , or another input. For operation as a digital multiplexer/demultiplexer, V_{EE} is connected to V_{SS} (typically ground). V_{EE} and V_{SS} are the supply voltage connections for the switches.

Features

- Wide supply voltage range from 3V to 9V
- Fully static operation
- 5 V and 9V parametric ratings
- Standardized symmetrical output characteristics
- Specified from - 40 C to + 85 C
- Packaging information: DIP16/ SOP16/ TSSOP16

Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
CD4053BE	DIP-16	CD4053BE	Tube	1000/Box
CD4053BDTR	SOP-16	CD4053B	Tape	2500/Reel
CD4053BDTR	TSSOP-16	CD4053B	Tape	3000/Reel

2、Block Diagram And Pin Description

2.1、Block Diagram

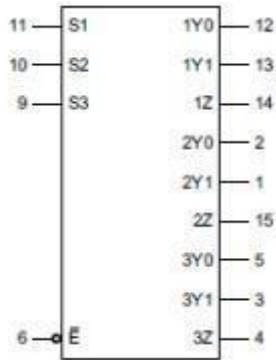


Figure 1 . Logic symbol



Figure 2 . Functional diagram

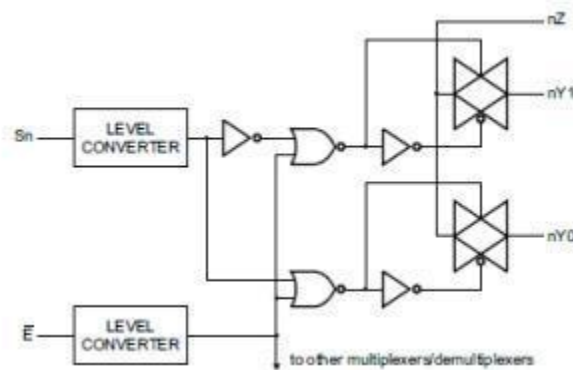


Figure 3 . Logic diagram (one multiplexer/ demultiplexer)

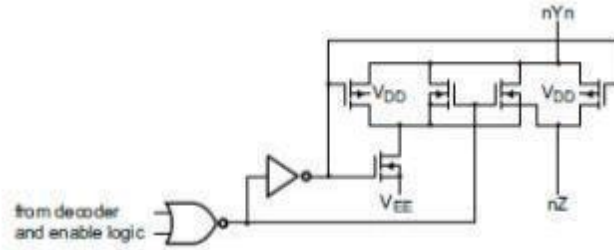
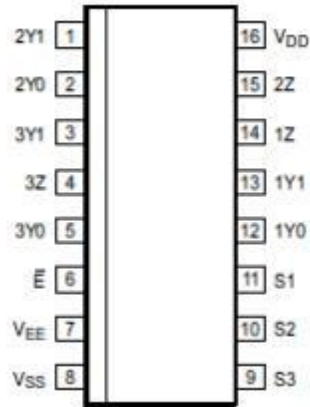


Figure 4 . Schematic diagram (one switch)

2.2、 Pin Configurations



2.3、 Pin Description

Pin No.	Pin Name	Description
1	2Y1	independent input or output
2	2Y0	independent input or output
3	3Y1	independent input or output
4	3Z	independent output or input
5	3Y0	independent input or output
6	\bar{E}	enable input (active LOW)
7	V_{EE}	supply voltage
8	V_{SS}	ground (0V)
9	S3	select input
10	S2	select input
11	S1	select input
12	1Y0	independent input or output
13	1Y1	independent input or output
14	1Z	independent output or input
15	2Z	independent output or input
16	V_{DD}	supply voltage

2.4、 Function Table

Input		Channel ON
\bar{E}	S_n	
L	L	nY0 to nZ
L	H	nY1 to nZ
H	X	switches off

Note: H=HIGH voltage level; L=LOW voltage level; X=don't care.

3 Electrical Parameter

3.1 Absolute Maximum Ratings

(Voltages are referenced to V_{SS} (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Max.	Unit
supply voltage	V_{DD}	-	-0.5	+12	V
power supply range	$V_{DD}-V_{EE}$	-	-0.5	+12	V
static current	I_Q	$V_{DD}-V_{EE}=12V$	-	2	uA
input voltage	V_I	-	-0.5	$V_{DD}+0.5$	V
output high voltage current	$ I_{IH} $	$V_{DD}=5V, V_I=V_{DD}$	-	1	uA
output low voltage current	$ I_{IL} $	$V_{DD}=5V, V_I=0V$	-	1	uA
input and output voltage range	V_{IO}	-	$V_{EE}-0.5$	$V_{DD}+0.5$	V
input clamping current	I_{IK}	$V_I < -0.5V$ or $V_I > V_{DD}+0.5V$	-	± 20	mA
input and output clamp current	I_{IOK}	$V_{IO} < V_{EE}-0.5V$ or $V_{IO} > V_{DD}+0.5V$	-	± 20	mA
switch conduction current	I_T	$V_O = -0.5V$ to $V_{DD}+0.5V$	-	± 25	mA
VDD or GND current	I_{DD}, I_{GND}	-	-	± 50	mA
storage temperature	T_{stg}	-	-65	+150	C
total power dissipation	P_{tot}	-	-	500	mW
Soldering temperature	T_L	10s	DIP	245	C
			SOP	250	C

Note:

[1] For DIP16 packages: above 70C the value of P_{tot} derates linearly with 12mW/K.

[2] For SOP16 packages: above 70C the value of P_{tot} derates linearly with 8mW/K.

[3] For (T)SSOP16 packages: above 60C the value of P_{tot} derates linearly with 5.5mW/K.

3.2 Recommended Operating Conditions

($T_{amb}=25C$; $R_L=10k\Omega$; $C_L=50pF$; $\bar{E}=V_{DD}$; $V_{is}=V_{DD}=5V$.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
supply voltage	V_{DD}	-	3	5	9	V
ambient temperature	T_{amb}	in free air	-40	-	+85	C
supply voltage	V_{EE}	-	-6.0	-	0	V
supply voltage	$V_{DD}-V_{EE}$	-	3.0	-	9.0	V
input voltage	V_I	-	0	-	V_{DD}	V
input and output voltage	V_{IO}	-	V_{EE}	-	V_{DD}	V
Input rise and fall time	t_r, t_f	-	-	-	1000	ns
		-	-	-	500	ns
		-	-	-	400	ns
input capacitance	C_I	-	-	-	7.5	pF

3.3、Electrical Characteristics

3.3.1、DC Characteristics 1

($T_{amb}=25C$, voltages are referenced to V_{SS} (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions (V)		$T_{amb}=25C$			Unit
				Min.	Typ.	Max.	
supply current	I_{DD}	$V_I=V_{DD}$ or $V_{SS}, I_O=0A$	$V_{DD}=5V$	-	-	20	μA
			$V_{DD}=9V$	-	-	40	μA
HIGH-level input voltage	V_{IH}	$ I_O <1\mu A$	$V_{DD}=5V$	3.5	-	-	V
			$V_{DD}=9V$	7.0	-	-	V
LOW-level input voltage	V_{IL}	$ I_O <1\mu A$	$V_{DD}=5V$	-	-	1.5	V
			$V_{DD}=9V$	-	-	3.0	V
input leakage current	I_I	$V_I=0V$ or $9V, V_{DD}=9V$		-	-	0.3	μA
3 state output leakage current	I_{OZ}	$V_{DD}=9V$	output to V_{DD}	-	-	1.6	μA
			output to V_{SS}	-	-	-1.6	μA
ON resistance (rail)	R_{ON}	$V_I=0V$ to $V_{DD}-V_{EE}$	$V_{DD}-V_{EE}=5V$	-	350	2500	Ω
			$V_{DD}-V_{EE}=9V$	-	80	245	Ω
		$V_I=0V$	$V_{DD}-V_{EE}=5V$	-	115	340	Ω
			$V_{DD}-V_{EE}=9V$	-	50	160	Ω
		$V_I=V_{DD}-V_{EE}$	$V_{DD}-V_{EE}=5V$	-	120	365	Ω
			$V_{DD}-V_{EE}=9V$	-	65	200	Ω
ON resistance mismatch between channels	ΔR_{ON}	$V_I=0V$ to $V_{DD}-V_{EE}$	$V_{DD}-V_{EE}=5V$	-	25	-	Ω
			$V_{DD}-V_{EE}=9V$	-	10	-	Ω
OFF-state leakage current	$I_{S(OFF)}$	$V_{SS}=V_{EE}, V_{DD}-V_{EE}=9V$	all channel off; $\bar{E}=V_{DD}$	-	-	1000	nA
			any channel; $\bar{E}=V_{SS}$	-	-	200	nA

Note: On resistance waveform and test circuit see Figure 12 and Figure 13.

3.3.2、DC Characteristics 2

($T_{amb}=-40C$ to $+85C$, voltages are referenced to V_{SS} (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions (V)		$T_{amb}=-40C$		$T_{amb}+85C$		Unit
				Min.	Max.	Min.	Max.	
supply current	I_{DD}	$V_I=V_{DD}$ or $V_{SS}, I_O=0A$	$V_{DD}=5V$	-	20	-	150	μA
			$V_{DD}=9V$	-	40	-	300	μA
HIGH-level input voltage	V_{IH}	$ I_O <1\mu A$	$V_{DD}=5V$	3.5	-	3.5	-	V
			$V_{DD}=9V$	7.0	-	7.0	-	V
LOW-level input voltage	V_{IL}	$ I_O <1\mu A$	$V_{DD}=5V$	-	1.5	-	1.5	V
			$V_{DD}=9V$	-	3.0	-	3.0	V
input leakage current	I_I	$V_I=0V$ or $9V, V_{DD}=9V$		-	0.3	-	1.0	μA
3 state output leakage current	I_{OZ}	$V_{DD}=9V$	output to V_{DD}	-	1.6	-	12.0	μA
			output to V_{SS}	-	-1.6	-	-12.0	μA

3.3.3、AC Characteristics 1

($T_{amb}=25C$, $V_{EE}=V_{SS}=0V$, t_r , $t_f \leq 20ns$, $C_L=50pF$, $R_L=10k\Omega$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
HIGH to LOW propagation delay time	t_{PHL}	Yn to Z; Z to Yn; see Figure 6	$V_{DD}=5V$	-	10	20	ns
			$V_{DD}=9V$	-	5	10	ns
		Sn to Yn, Z; see Figure 7	$V_{DD}=5V$	-	150	305	ns
			$V_{DD}=9V$	-	65	135	ns
LOW to HIGH propagation delay	t_{PLH}	Yn to Z; Z to Yn; see Figure 6	$V_{DD}=5V$	-	10	20	ns
			$V_{DD}=9V$	-	5	10	ns
		Sn to Yn, Z; see Figure 7	$V_{DD}=5V$	-	150	300	ns
			$V_{DD}=9V$	-	75	150	ns
HIGH to OFF-state propagation delay	t_{PHZ}	\bar{E} to Yn, Z; see Figure 8	$V_{DD}=5V$	-	95	190	ns
			$V_{DD}=9V$	-	90	180	ns
LOW to OFF-state propagation delay	t_{PLZ}	\bar{E} to Yn, Z; see Figure 8	$V_{DD}=5V$	-	100	205	ns
			$V_{DD}=9V$	-	90	180	ns
OFF-state to HIGH propagation delay	t_{PZH}	\bar{E} to Yn, Z; see Figure 8	$V_{DD}=5V$	-	130	260	ns
			$V_{DD}=9V$	-	55	115	ns
OFF-state to LOW propagation delay	t_{PZL}	\bar{E} to Yn, Z; see Figure 8	$V_{DD}=5V$	-	120	240	ns
			$V_{DD}=9V$	-	50	100	ns

3.3.4、AC Characteristics 2

($T_{amb}=25C$, $V_{EE}=V_{SS}=0V$, $V_I=0.5V_{DD}$ (p-p), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Square wave distortion	d_{sin}	see Figure 9; $R_L=10k\Omega$; $C_L=15pF$; channel ON; $f_i=1kHz$	$V_{DD}=5V$	0.25	-	-	%
			$V_{DD}=9V$	0.04	-	-	%
any two channel crosstalk	f_{ct}	$V_{DD}=9V$, see note2	1	-	-	MHz	
crosstalk voltage (\bar{E} to Sn or Yn to Z)	V_{ct}	see Figure 10; $R_L=10k\Omega$; $C_L=15pF$; \bar{E} or Sn= V_{DD} (square-wave)	50	-	-	mV	
OFF frequency	f_{OFF}	$V_{DD}=9V$, see note3	1	-	-	MHz	
conduction frequency	f_{ON}	$V_{DD}=5V$, see note4	13	-	-	MHz	
		$V_{DD}=9V$, see note4	40	-	-	MHz	

Note:

- [1] f_i is biased at $0.5V_{DD}$; $V_I=0.5V_{DD}$ (p-p).
- [2] $R_L=1k\Omega$; $20\log V_{os}/V_{is}=-50dB$, see Figure 11.
- [3] $R_L=1k\Omega$; $C_L=5pF$, channel off, $20\log V_{os}/V_{is}=-50dB$, see Figure 9.
- [4] $R_L=1k\Omega$; $C_L=5pF$, channel on, $20\log V_{os}/V_{is}=-3dB$, see Figure 9.

4、Testing Circuit

4.1、AC Testing Circuit 1

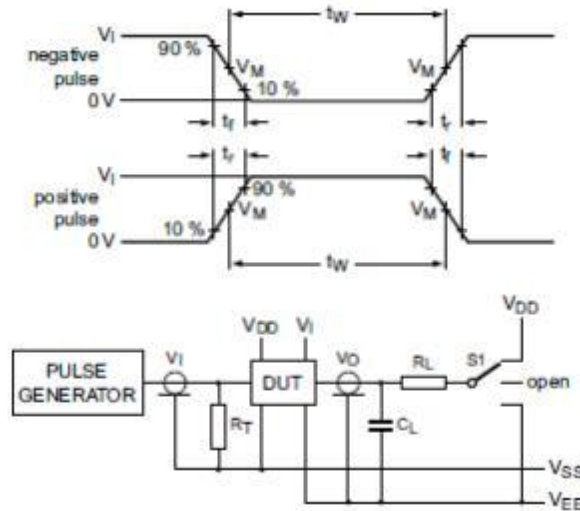


Figure 5. Test circuit for switching times

Definitions for test circuit:

DUT=Device Under Test.

C_L =Load capacitance including jig and probe capacitance.

R_T =Termination resistance should be equal to the output impedance Z_o of the pulse generator. R_L =Load resistance.

4.2、AC Testing Waveforms

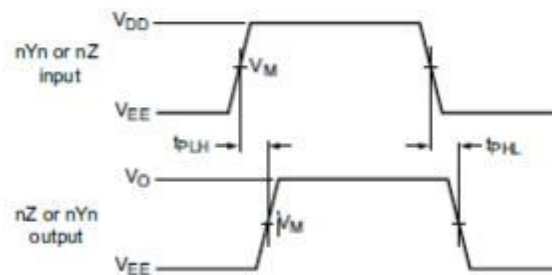


Figure 6. nYn, nZ to nZ, nYn propagation delays

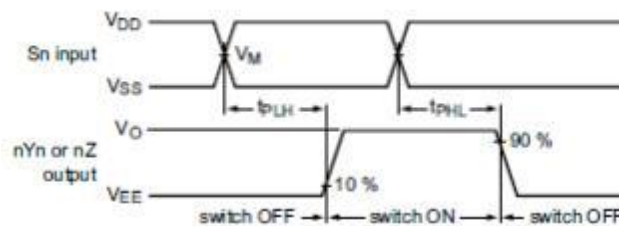


Figure 7. S_n to nYn, nZ propagation delays

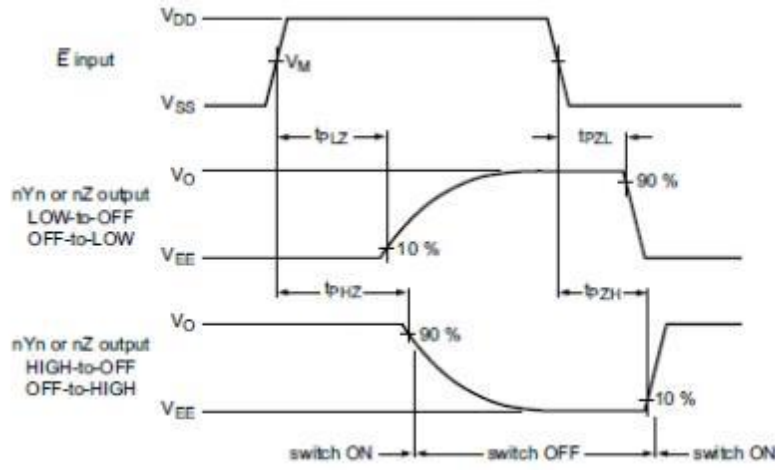


Figure 8. Enable and disable times

4.3、AC Testing Circuit 2

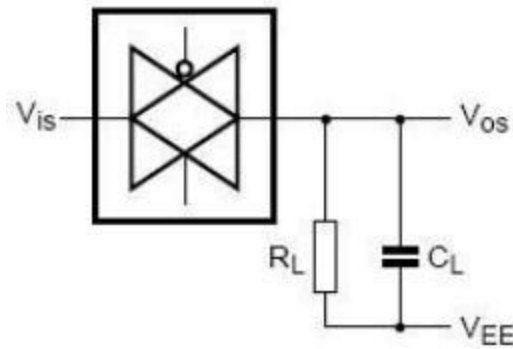


Figure 9. Square wave distortion degree of cut-off frequency and conduction frequency test pattern

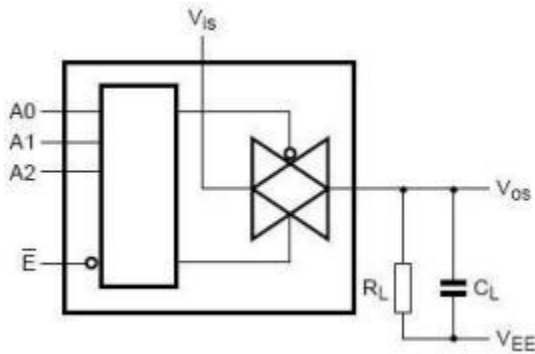


Figure 10. Crosstalk logical input/output test

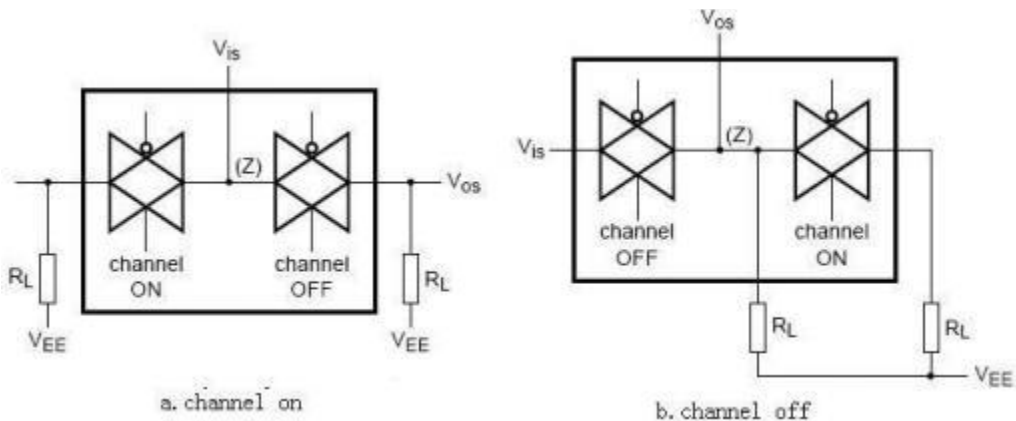


Figure 11. Inter channel Crosstalk

4.4、 On Resistance Waveform And Test Circuit

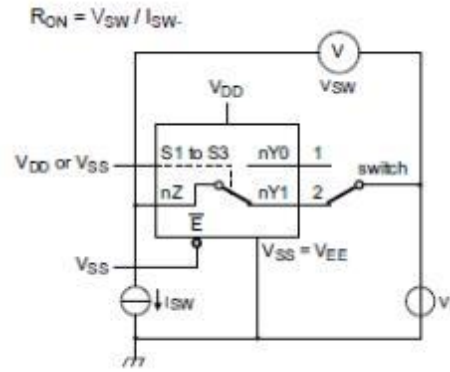


Figure 12. Test circuit for measuring R_{ON}

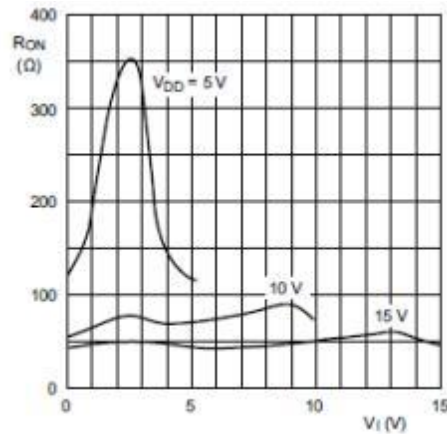


Figure 13. Typical R_{ON} as a function of input voltage

4.5、 Measurement Points

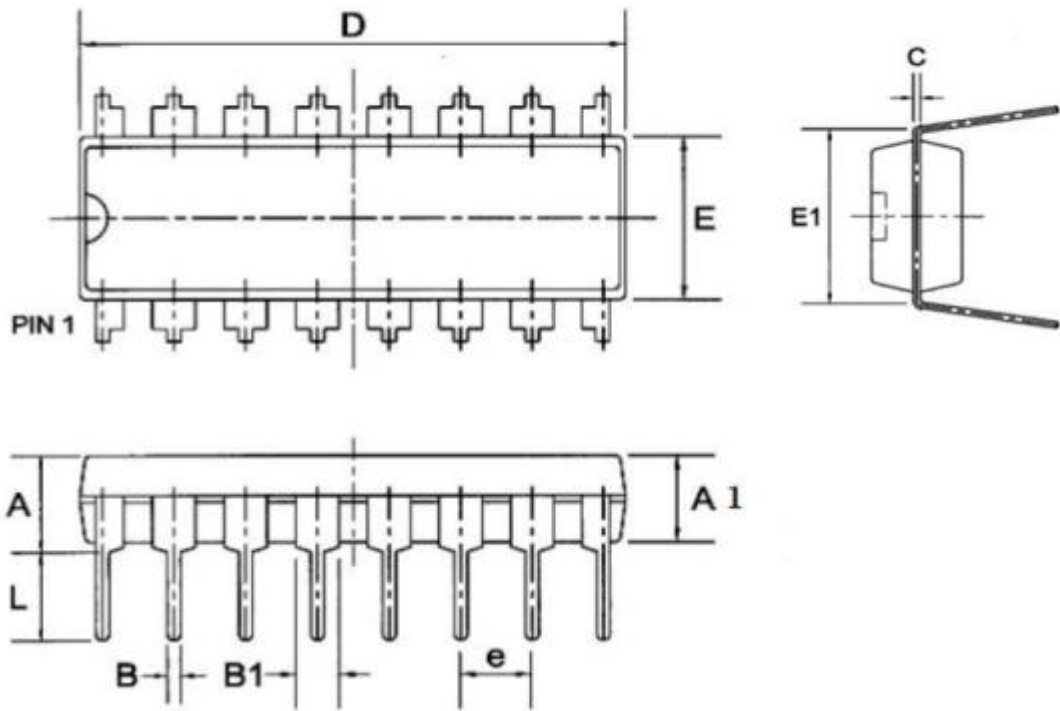
Supply voltage	Input	Output
V_{DD}	V_M	V_M
3V to 9V	$0.5 \times V_{DD}$	$0.5 \times V_{DD}$

4.6、 Test Data

Test	Input		Load		Switch
	V_{is}	t_r, t_f	C_L	R_L	
t_{PHL}	V_{EE}	20ns	50pF	10kΩ	V_{DD}
t_{PLH}	V_{DD}	20ns	50pF	10kΩ	V_{EE}
t_{PZH}, t_{PHZ}	V_{DD}	20ns	50pF	10kΩ	V_{EE}
t_{PZL}, t_{PLZ}	V_{EE}	20ns	50pF	10kΩ	V_{DD}
others	pulse	20ns	50pF	10kΩ	open

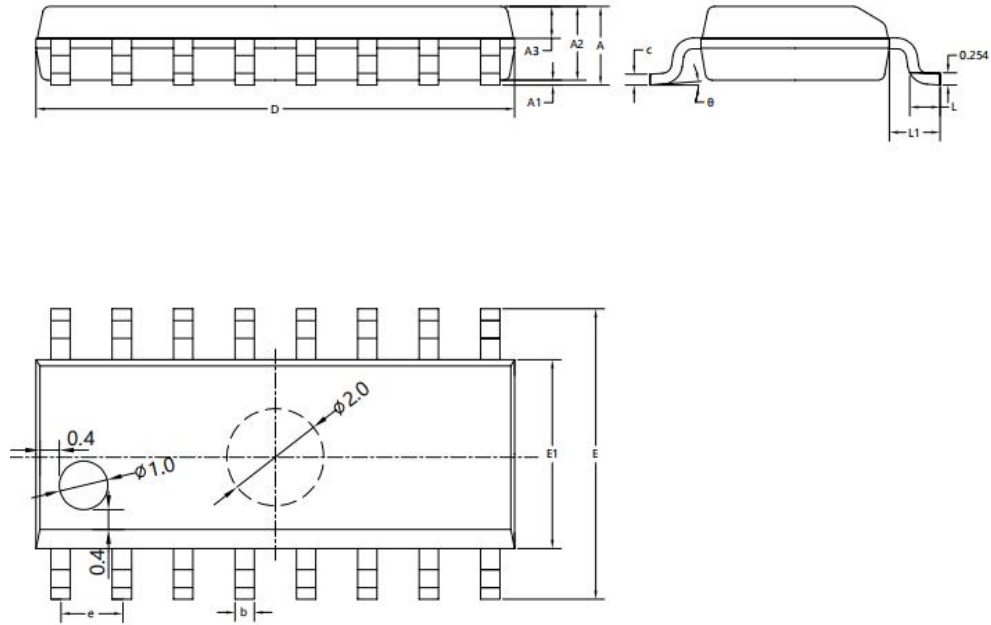
5、Package Information

5.1 DIP16



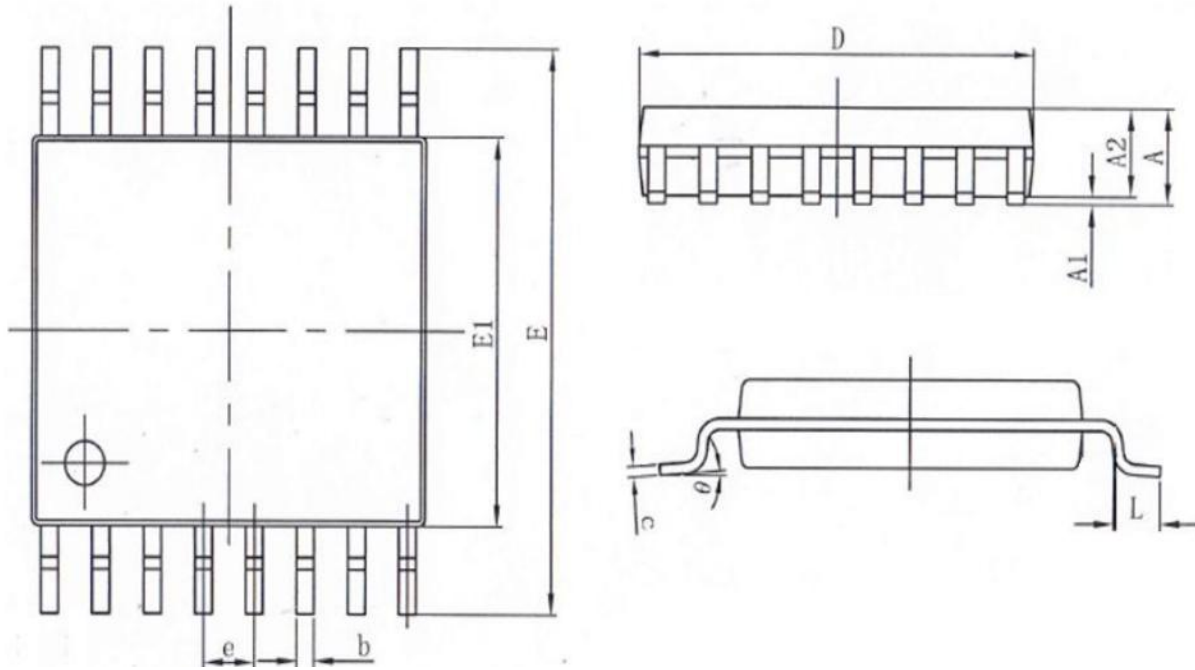
Symbol	Dimensions in Millimeters		
	Min	Nom	Max
A	--	--	4.31
A1	3.15	3.30	3.65
B	--	0.50	--
B1	--	1.6	--
C	--	0.27	--
D	19.00	19.20	19.60
E	6.20	6.50	6.60
E1	--	8.0	--
e	--	2.3	--
L	3.00	3.20	3.60

5.2 SOP16



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	1.50	1.60	1.70
A1	0.10	0.15	0.25
A2	1.40	1.45	1.50
A3	0.60	0.65	0.70
b	0.30	0.40	0.50
c	0.15	0.20	0.25
D	9.80	9.90	10.00
E	5.80	6.00	6.20
E1	3.85	3.90	3.95
e	1.27BSC		
L	0.50	0.60	0.70
L1	1.05BSC		
θ	0°	4°	8°

5.3 TSSOP16



SYMBOL	MILLIMETER	
	MIN	MAX
A	-	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E1	4.30	4.50
E	6.20	6.60
e	0.65	
L	0.45	0.75
θ	0°	8°

Statement:

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